HD74ALVC1G00

2–input NAND Gate

HITACHI

ADE-205-604A (Z)
2nd. Edition
March 2001

Description

The HD74ALVC1G00 has two–input NAND gate in a 5 pin package. Low voltage and high speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

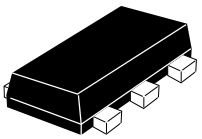
Features

- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- Supply voltage range : 1.2 to 3.6 V
  Operating temperature range : –40 to +85°C
- All inputs V_{IH} (Max.) = 3.6 V (@V_{CC} = 0 V to 3.6 V)
  All outputs V_O (Max.) = 3.6 V (@V_{CC} = 0 V)
- Output current ±2 mA (@V_{CC} = 1.2 V)
  ±4 mA (@V_{CC} = 1.4 V to 1.6 V)
  ±6 mA (@V_{CC} = 1.65 V to 1.95 V)
  ±18 mA (@V_{CC} = 2.3 V to 2.7 V)
  ±24 mA (@V_{CC} = 3.0 V to 3.6 V)

Hitachi semiconductor

Outline and Article Indication

• HD74ALVC1G00



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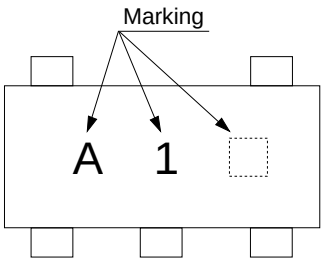


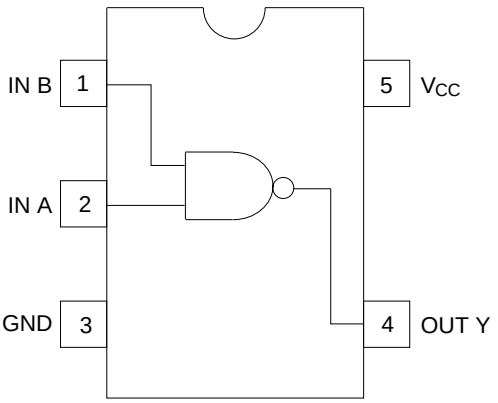
Function Table

Inputs		Output Y
A	**B**	
L	L	H
L	H	H
H	L	H
H	H	L

H : High level

L : Low level

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V_{CC}	–0.5 to 4.6	V	
Input voltage range [*1]	V_I	–0.5 to 4.6	V	
Output voltage range [*1, 2]	V_O	–0.5 to V_{CC} + 0.5	V	Output : H or L
		–0.5 to 4.6		V_{CC} : OFF
Input clamp current	I_{IK}	–50	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±50	mA	V_O = 0 to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) [*3]	P_T	200	mW	
Storage temperature	Tstg	–65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V_{CC}	1.2	3.6	V	
Input voltage range	V_I	0	3.6	V	
Output voltage range	V_O	0	V_{CC}	V	
Output current	I_{OH}	—	–2	mA	V_{CC} = 1.2 V
		—	–4		V_{CC} = 1.4 V
		—	–6		V_{CC} = 1.65 V
		—	–18		V_{CC} = 2.3 V
		—	–24		V_{CC} = 3.0 V
	I_{OL}	—	2		V_{CC} = 1.2 V
		—	4		V_{CC} = 1.4 V
		—	6		V_{CC} = 1.65 V
		—	18		V_{CC} = 2.3 V
		—	24		V_{CC} = 3.0 V
Input transition rise or fall rate	$\Delta t / \Delta v$	0	20	ns / V	V_{CC} = 1.2 to 2.7 V
		0	10		V_{CC} = 3.3±0.3 V
Operating free-air temperature	T_a	–40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristic

- **Ta = –40 to 85°C**

Item	Symbol	V_{cc} (V) *	Min	Typ	Max	Unit	Test condition
Input voltage	V_{IH}	1.2	V_{CC}×0.75	—	—	V	
		1.4 to 1.6	V_{CC}×0.7	—	—		
		1.65 to 1.95	V_{CC}×0.7	—	—		
		2.3 to 2.7	1.7	—	—		
		3.0 to 3.6	2.0	—	—		
	V_{IL}	1.2	—	—	V_{CC}×0.25		
		1.4 to 1.6	—	—	V_{CC}×0.3		
		1.65 to 1.95	—	—	V_{CC}×0.3		
		2.3 to 2.7	—	—	0.7		
		3.0 to 3.6	—	—	0.8		
Output voltage	V_{OH}	Min to Max	V_{CC}–0.2	—	—	V	I_{OH} = –100 µA
		1.2	0.9	—	—		I_{OH} = –2 mA
		1.4	1.1	—	—		I_{OH} = –4 mA
		1.65	1.2	—	—		I_{OH} = –6 mA
		2.3	1.7	—	—		I_{OH} = –18 mA
		3.0	2.2	—	—		I_{OH} = –24 mA
	V_{OL}	Min to Max	—	—	0.2		I_{OL} = 100 µA
		1.2	—	—	0.3		I_{OL} = 2 mA
		1.4	—	—	0.3		I_{OL} = 4 mA
		1.65	—	—	0.3		I_{OL} = 6 mA
		2.3	—	—	0.55		I_{OL} = 18 mA
		3.0	—	—	0.55		I_{OL} = 24 mA
Input current	I_{IN}	3.6	—	—	±5	µA	V_{IN} = 3.6 V or GND
Quiescent supply current	I_{CC}	3.6	—	—	10	µA	V_{IN} = V_{CC} or GND, I_O = 0
Output leakage current	I_{OFF}	0	—	—	5	µA	V_I or V_O = 0 to 3.6 V
Input capacitance	C_{IN}	3.3	—	2.5	—	pF	V_{IN} = V_{CC} or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

- V_{CC} = 1.2 V

Item	Symbol	T_a = –40 to 85°C			Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max				
Propagation delay time	t_{PLH} t_{PHL}	—	7.5	—	ns	C_L = 15 pF	A or B	Y

- V_{CC} = 1.5 ± 0.1 V

Item	Symbol	T_a = –40 to 85°C			Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max				
Propagation delay time	t_{PLH} t_{PHL}	2.0	—	8.0	ns	C_L = 15 pF	A or B	Y

- V_{CC} = 1.8 ± 0.15 V

Item	Symbol	T_a = –40 to 85°C			Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max				
Propagation delay time	t_{PLH} t_{PHL}	1.5	—	6.0	ns	C_L = 30 pF	A or B	Y

- V_{CC} = 2.5 ± 0.2 V

Item	Symbol	T_a = –40 to 85°C			Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max				
Propagation delay time	t_{PLH} t_{PHL}	1.0	—	3.7	ns	C_L = 30 pF	A or B	Y

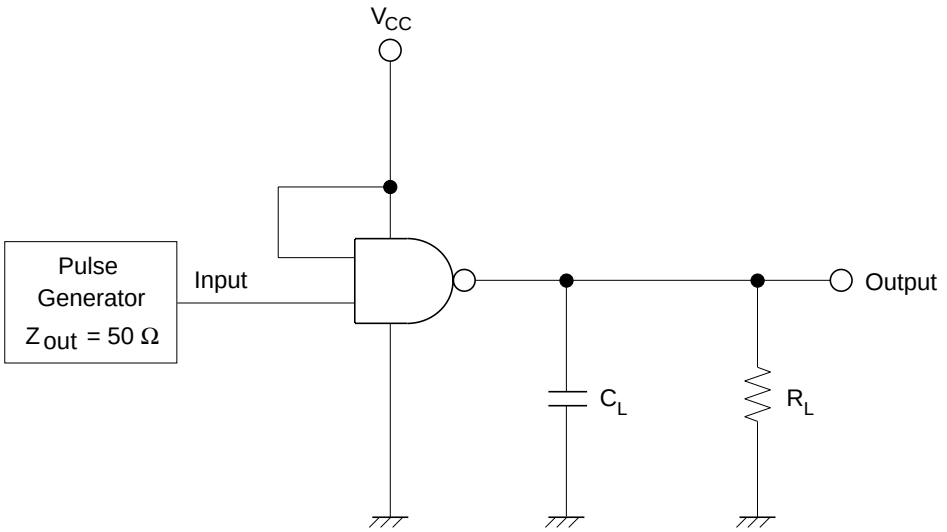
- V_{CC} = 3.3 ± 0.3 V

Item	Symbol	T_a = –40 to 85°C			Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max				
Propagation delay time	t_{PLH} t_{PHL}	1.0	—	2.8	ns	C_L = 30 pF	A or B	Y

Operating Characteristics

Item	Symbol	V_{CC} (V)	T_a = 25°C			Unit	Test Conditions
			Min	Typ	Max		
Power dissipation capacitance	C_{PD}	1.5	—	10.5	—	pF	f = 10 MHz
		1.8	—	10.5	—		
		2.5	—	10.5	—		
		3.3	—	11.5	—		

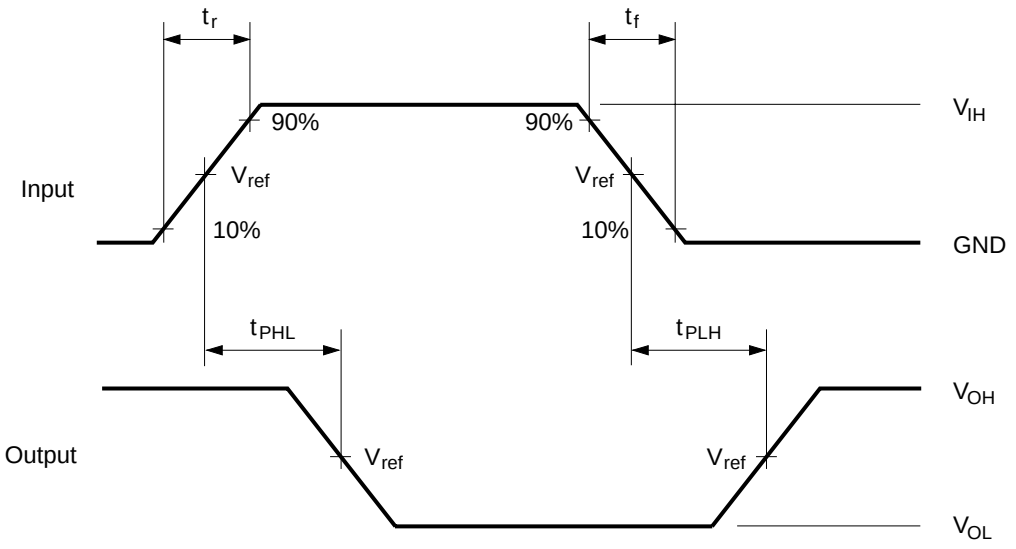
Test Circuit



Symbol	V_{CC} = 1.2 V, 1.5±0.1 V	V_{CC} = 1.8±0.15 V	V_{CC} = 2.5±0.2 V, 3.3±0.3 V
R_L	2.0 kΩ	1.0 kΩ	500 Ω
C_L	15 pF	30 pF	30 pF

Note: C_L includes probe and jig capacitance.

• **Waveforms**



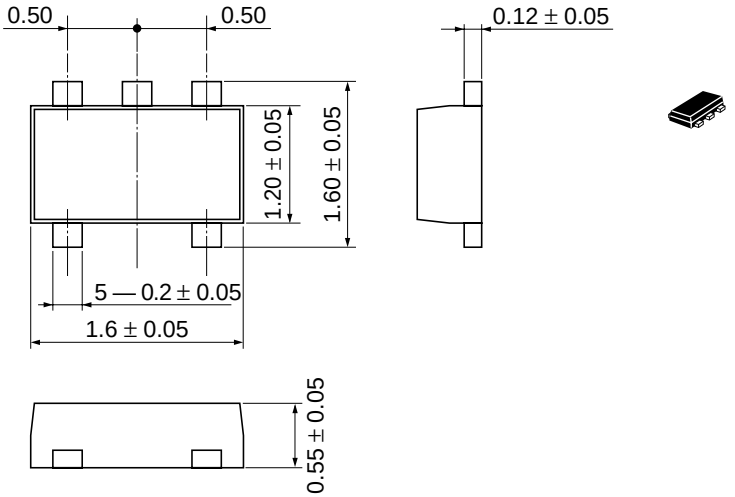
Symbol	V_{CC} = 1.2 V, 1.5±0.1 V, 1.8±0.15 V	V_{CC} = 2.5±0.2 V	V_{CC} = 3.3±0.3 V
t_r / t_f	2.0 ns	2.5 ns	2.5 ns
V_{IH}	V_{CC}	V_{CC}	2.7 V
V_{ref}	50%	50%	1.5 V

Note: Input waveform : PRR = 10 MHz, duty cycle 50%

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TNP-5D
JEDEC	—
EIAJ	—
Mass (reference value)	—

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585200

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
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